Photo Semiconductor Device - Page 1 of 1



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Inclosure Material: Ceramic and metal and glass **Overall Length:** 0.087 inches **Overall Diameter:** 0.088 inches **Function For Which Designed:** Detector Internal Configuration: Junction contact **Mounting Method:** Terminal **Features Provided:** Hermetically sealed case **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 50.0 collector to emitter voltage, dc and 7.0 emitter to collector voltage, dc **Current Rating Per Characteristic:** 25.00 nanoamperes repetitive peak forward current peak **Power Rating Per Characteristic:** 50.0 milliwatts small-signal input power, common-collector preset Maximum Operating Tempurature Per Measurement Point: 150.0 degrees celsius ambient air **Special Features:** Junction pattern arrangement: npn **Precious Material And Location:** Case surface gold **Precious Material:** Gold **Terminal Type And Quantity:** 1 case and 2 tab, solder lug Shelf Life: N/a Unit Of Measure: Demilitarization: No Fiig: A110a0